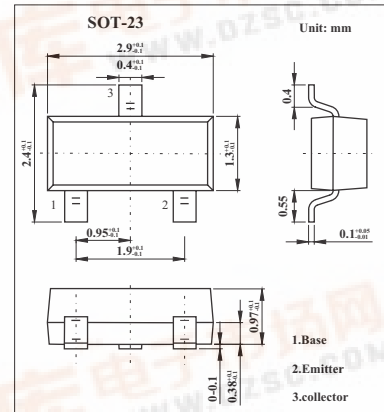


SMD Type Transistors

PNP Transistor
KST9012

■ Features

- Excellent hFE linearity
- Collector Current :Ic=-0.5A



■ Absolute Maximum Ratings Ta = 25°C

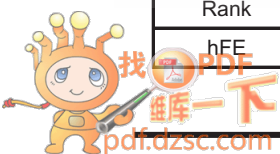
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-40	V
Collector - Emitter Voltage	V _{CEO}	-25	V
Emitter - Base Voltage	V _{EBO}	-5	V
Collector Current to Continuous	I _c	-500	mA
Collector Power Dissipation	P _c	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector - base breakdown voltage	V _{CB0}	I _c = -100μA, I _E =0	-40			V
Collector - emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-25			V
Emitter - base breakdown voltage	V _{EBO}	I _E = -100μA, I _c =0	-5			V
Collector cut - off current	I _{CB0}	V _{CB} =- 40V, I _E =0			-0.1	μ A
Collector cut - off current	I _{CEO}	V _{CB} =-20V, I _E =0			-0.1	μ A
Emitter cut - off current	I _{EBO}	V _{EB} =- 5V, I _c =0			-0.1	μ A
DC current gain	h _{FE}	V _{CE} =-1V, I _c = -50mA	120		400	
Collector - emitter saturation voltage	V _{CE(sat)}	I _c = -500 mA, I _B = -50mA			-0.6	V
Base - emitter voltage	V _{BE(sat)}	I _c = -500 mA, I _B =- 50mA			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			5	pF
Transition frequency	f _T	V _{CE} =-6V, I _c =-20mA, f=30MHz	150			MHz

■ hFE Classification

Marking	2T1		
Rank	L	H	J
hFE	120~200	200~350	300~400



KST9012

■ Typical Characteristics

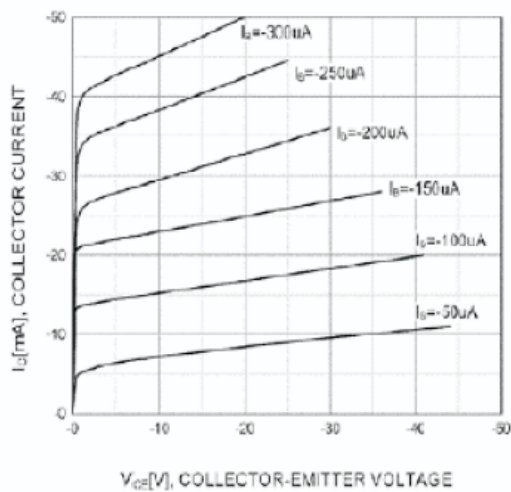


Fig.1 Static Characteristic

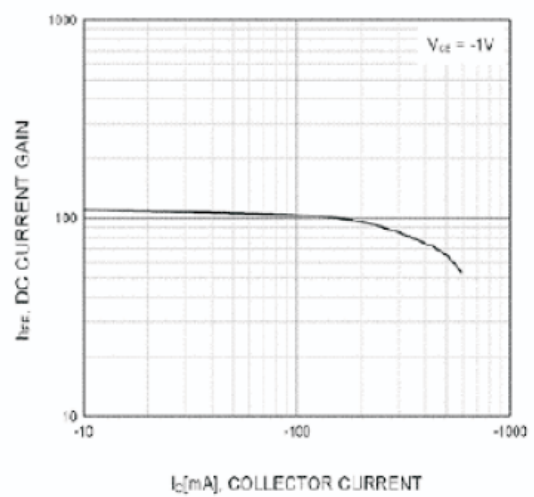


Fig.2 DC Current Gain

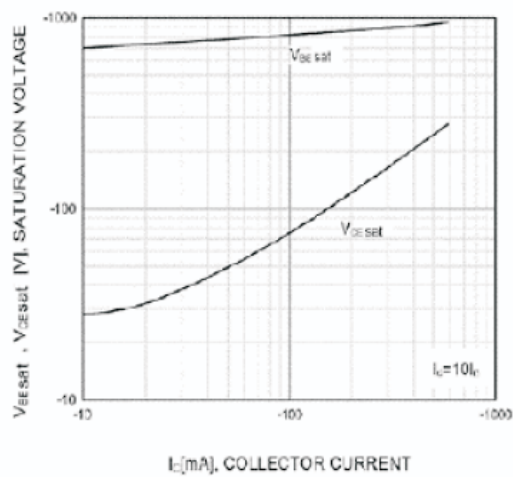


Fig.3 Base-Emitter Saturation Voltage
Collector- Emitter Saturation Voltage

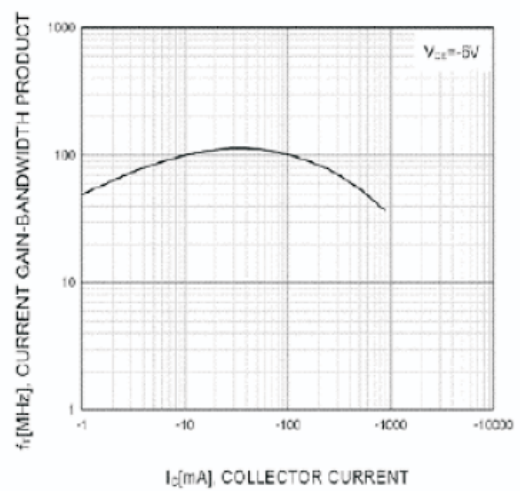


Fig.4 Current Gain Bandwidth Product